

MMWMC Panel Session

Topic: Which MMIC Technology Will Win the PCN Race?
Date: Monday, June 14, 1993
Time: 12:00 pm–1:30 pm
Location: Room 314
Moderator: Sanjay Moghe, Northrop ESD

Abstract:

Personal Communications Networks are expected to represent a huge market for RF components in coming years. A number of MMIC components in silicon, GaAs MESFET and GaAs HBT technologies are now becoming available for PCN application. Silicon bipolar and MOS based technologies are generally regarded as low risk and low cost for frequency applications below 1 GHz, and have shown a lot of promise with digital and microwave parts integrated on the same chip. GaAs-based circuits, however, have shown some of the highest levels of integration for PCN transceiver applications with amplifier, oscillators, mixers, power amplifiers, and synthesizers all on a single chip. Industry experts will discuss in depth the trade-offs among the competing technologies in performance, cost, reliability and time-to-market.